



#### PNP MEDIUM POWER TRANSISTORS IN SOT223

#### **Features**

- BV<sub>CEO</sub> > -45V, -60V & -80V
- I<sub>C</sub> = -1A High Continuous Collector Current
- I<sub>CM</sub> = -2A Peak Pulse Current
- 2W Power Dissipation
- Low Saturation Voltage V<sub>CE(sat)</sub> < -500mV @ -0.5A</li>
- Gain Groups 10 and 16
- Complementary NPN types: BCP54, 55 and 56
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Mechanical Data**

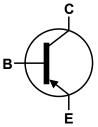
- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (approximate)

#### **Applications**

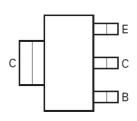
- Medium Power Switching or Amplification Applications
- AF Driver and Output Stages







Device Symbol



Top View Pin-Out

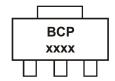
### Ordering Information (Notes 4 & 5)

| Product   | Compliance | Marking  | Reel size (inches) | Tape width (mm) | Quantity per reel |
|-----------|------------|----------|--------------------|-----------------|-------------------|
| BCP51TA   | AEC-Q101   | BCP 51   | 7                  | 12              | 1,000             |
| BCP5110TA | AEC-Q101   | BCP 5110 | 7                  | 12              | 1,000             |
| BCP5116TA | AEC-Q101   | BCP 5116 | 7                  | 12              | 1,000             |
| BCP5116TC | AEC-Q101   | BCP 5116 | 13                 | 12              | 4,000             |
| BCP52TA   | AEC-Q101   | BCP 52   | 7                  | 12              | 1,000             |
| BCP5210TA | AEC-Q101   | BCP 5210 | 7                  | 12              | 1,000             |
| BCP5216TA | AEC-Q101   | BCP 5216 | 7                  | 12              | 1,000             |
| BCP53TA   | AEC-Q101   | BCP 53   | 7                  | 12              | 1,000             |
| BCP53QTA  | Automotive | BCP 53   | 7                  | 12              | 1,000             |
| BCP5310TA | AEC-Q101   | BCP 5310 | 7                  | 12              | 1,000             |
| BCP5316TA | AEC-Q101   | BCP 5316 | 7                  | 12              | 1,000             |
| BCP5316TC | AEC-Q101   | BCP 5316 | 13                 | 12              | 4,000             |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
- 5. For packaging details, go to our website at http://www.diodes.com

### **Marking Information**



BCP = Product Type Marking Code, Line 1. xxxx = Product Type Marking Code, Line 2 as follows:

 BCP51
 = 51
 BCP52
 = 52
 BCP53
 = 53

 BCP5110
 = 5110
 BCP5210
 = 5210
 BCP5310
 = 5310

 BCP5116
 = 5116
 BCP5216
 = 5216
 BCP5316
 = 5316



#### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic               | Symbol           | BCP51 | BCP52 | BCP53 | Unit  |  |
|------------------------------|------------------|-------|-------|-------|-------|--|
| Collector-Base Voltage       | V <sub>CBO</sub> | -45   | -60   | -100  | V     |  |
| Collector-Emitter Voltage    | V <sub>CEO</sub> | -45   | -60   | -80   | V     |  |
| Emitter-Base Voltage         | $V_{EBO}$        |       | -5    |       |       |  |
| Continuous Collector Current | Ic               |       | -1    |       |       |  |
| Peak Pulse Collector Current | I <sub>CM</sub>  |       | -2    |       |       |  |
| Continuous Base Current      | I <sub>B</sub>   |       | -100  |       |       |  |
| Peak Pulse Base Current      | I <sub>BM</sub>  | -200  |       |       | mA mA |  |

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

| Characteristic                                 | Symbol                           | Value            | Unit |      |
|--|----------------------------------|------------------|------|------|
| Power Dissipation                              | (Note 6)                         | P <sub>D</sub>   | 2    | W    |
| Thermal Resistance, Junction to Ambient        | (Note 6)                         | R <sub>0JA</sub> | 62   | °C/W |
| Thermal Resistance, Junction to Leads (Note 7) |                                  | $R_{\theta JL}$  | 19.4 | °C/W |
| Operating and Storage Temperature Range        | T <sub>J,</sub> T <sub>STG</sub> | -65 to +150      | °C   |      |

# ESD Ratings (Note 8)

| Characteristic                             | Symbol  | Value   | Unit | JEDEC Class |
|--|---------|---------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | ≥ 4,000 | V    | 3A          |
| Electrostatic Discharge - Machine Model    | ESD MM  | ≥ 400   | V    | С           |

Notes:

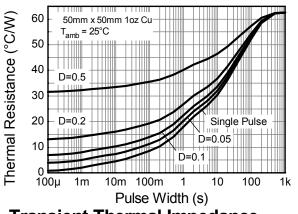
<sup>6.</sup> For a device surface mounted on 50mm X 50mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; device measured when operating in steady state condition.

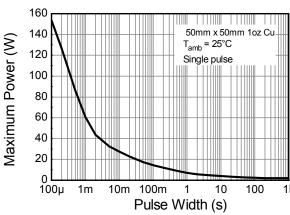
7. Thermal resistance from junction to solder-point (at the end of the collector lead).

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



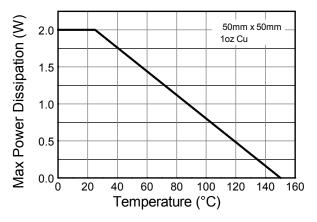
## **Thermal Characteristics and Derating Information**





# **Transient Thermal Impedance**

**Pulse Power Dissipation** 



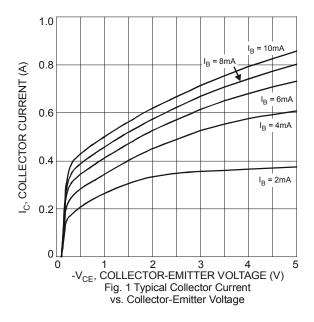
**Derating Curve** 



# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                  | Symbol                  | Min                  | Тур               | Max | Unit          | Test Condition |  |
|---|-------------------------|----------------------|-------------------|-----|---------------|----------------|--|
| Collector-Base<br>Breakdown Voltage             | BCP51<br>BCP52          | BV <sub>CBO</sub>    | -45<br>-60        | -   | -             | V              | I <sub>C</sub> = -100μA  |
|   | BCP53<br>BCP51          |                      | -100              |     |               |                |  |
| Collector-Emitter<br>Breakdown Voltage (Note 9) | BCP51<br>BCP52<br>BCP53 | BV <sub>CEO</sub>    | -45<br>-60<br>-80 | -   | -             | V              | I <sub>C</sub> = -10mA   |
| Emitter-Base Breakdown Voltage                  |                         | BV <sub>EBO</sub>    | -5                | -   | -             | V              | I <sub>E</sub> = -10μA   |
| Collector Cut-off Current                       |                         | I <sub>CBO</sub>     | -                 | -   | -0.1<br>-20   | μA             | V <sub>CB</sub> = -30V<br>V <sub>CB</sub> = -30V, T <sub>A</sub> = +150°C                        |
| Emitter Cut-off Current                         |                         | I <sub>EBO</sub>     | -                 | -   | -20           | nA             | V <sub>EB</sub> = -4V  |
| Static Forward Current Transfer Ratio (Note 9)  | All versions            | h <sub>FE</sub>      | 25<br>40<br>25    |     | -<br>250<br>- | -              | $I_C$ = -5mA, $V_{CE}$ = -2V<br>$I_C$ = -150mA, $V_{CE}$ = -2V<br>$I_C$ = -500mA, $V_{CE}$ = -2V |
| , , ,   | 10 gain grp             |                      | 63                | -   | 160           |                | I <sub>C</sub> = -150mA, V <sub>CE</sub> = -2V   |
|   | 16 gain grp             |                      | 100               | -   | 250           |                | $I_C = -150 \text{mA}, V_{CE} = -2 \text{V}$   |
| Collector-Emitter Saturation Voltage (Note 9)   |                         | V <sub>CE(sat)</sub> | -                 | -   | -0.5          | V              | $I_C = -500$ mA, $I_B = -50$ mA  |
| Base-Emitter Turn-On Voltage (Note 9)           |                         | V <sub>BE(on)</sub>  | ı                 | -   | -1.0          | V              | $I_C = -500 \text{mA}, V_{CE} = -2 \text{V}$   |
| Transition Frequency                            |                         | f⊤                   | 150               | -   | -             | MHz            | $I_C$ = -50mA, $V_{CE}$ = -10V<br>f = 100MHz   |
| Output Capacitance                              |                         | Cobo                 | -                 | -   | 25            | pF             | V <sub>CB</sub> = -10V, f = 1MHz   |

Notes: 9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



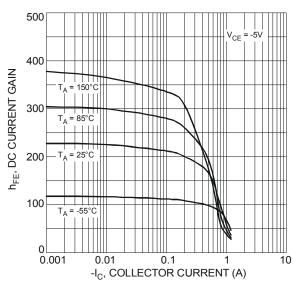


Fig. 2 Typical DC Current Gain vs. Collector Current



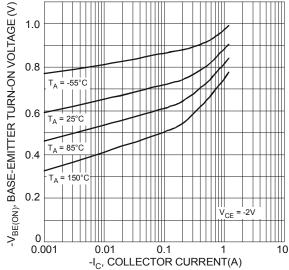


Fig 3 Typical Base-Emitter Turn-On Voltage vs. Collector Current

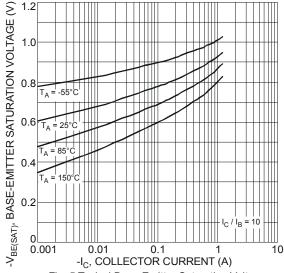


Fig. 5 Typical Base-Emitter Saturation Voltage vs. Collector Current

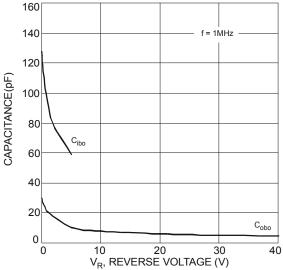


Fig. 7 Typical Capacitance Characteristics

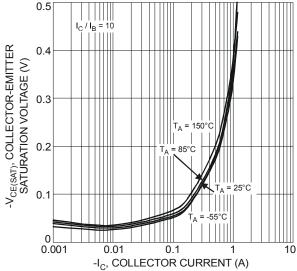


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

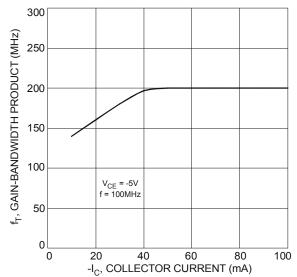
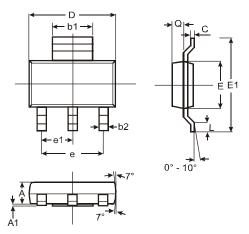


Fig. 6 Typical Gain-Bandwidth Product vs. Collector Current



# **Package Outline Dimensions**

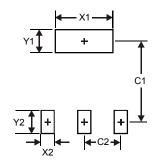
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



| SOT223               |       |      |      |  |  |
|----------------------|-------|------|------|--|--|
| Dim                  | Min   | Max  | Тур  |  |  |
| Α                    | 1.55  | 1.65 | 1.60 |  |  |
| A1                   | 0.010 | 0.15 | 0.05 |  |  |
| b1                   | 2.90  | 3.10 | 3.00 |  |  |
| b2                   | 0.60  | 0.80 | 0.70 |  |  |
| С                    | 0.20  | 0.30 | 0.25 |  |  |
| D                    | 6.45  | 6.55 | 6.50 |  |  |
| Е                    | 3.45  | 3.55 | 3.50 |  |  |
| E1                   | 6.90  | 7.10 | 7.00 |  |  |
| е                    | _     |      | 4.60 |  |  |
| e1                   | _     | _    | 2.30 |  |  |
| L                    | 0.85  | 1.05 | 0.95 |  |  |
| Q                    | 0.84  | 0.94 | 0.89 |  |  |
| All Dimensions in mm |       |      |      |  |  |

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| X1         | 3.3           |
| X2         | 1.2           |
| Y1         | 1.6           |
| Y2         | 1.6           |
| C1         | 6.4           |
| C2         | 2.3           |



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